

A Legacy of Innovation

KIOXIA¹ delivers flash-based products for next generation storage applications. With a steadfast commitment to technology innovation, KIOXIA will continue to push the boundaries of what's possible.

A LOOK BACK: OVER THREE DECADES OF INNOVATION²

1987

Invented NAND Flash Memory



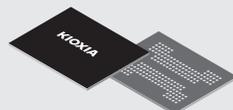
1991

World's 1st Mass Production of NAND Flash Memory



2001

1st to Introduce Commercial 1Gb MLC NAND



2007

World's 1st 3D Flash Memory Technology Announced



2013

World's first UFS Introduced



2014

World's 1st 15nm 128Gb NAND Flash Memory Introduced



2015

World's 1st 48-layer 3D Flash Memory

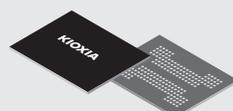


“Changing the world through innovative solutions.”

*Nobuo Hayasaka
President and CEO, KIOXIA Corporation*

2017

1st to Introduce 4-bit-per-cell Technology (QLC BiCS FLASH 3D Flash Memory)



2018

Mass Production of 96-layer 3D Flash Memory



Achieved Industry's Highest Capacity of 1.33 Terabits for a single chip (QLC BiCS FLASH)



2019

1st to Sample UFS Version 3.0



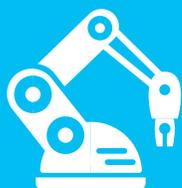
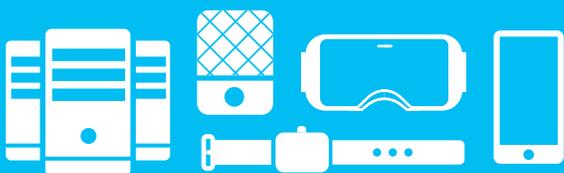
2020

Introduced 112-Layer 3D Flash Memory Technology

By 2024, worldwide data volume is expected to reach **143 zettabytes** (source IDC⁴)

KIOXIA Makes Data Work – Innovation in Action

INNOVATION STARTS WITH KIOXIA



THE INVENTOR OF FLASH MEMORY